

SANYO

No.819D

DRA5

Silicon Diffused Junction Type

5.0A Reverse Blocking Thyristor

Features

- Glass passivation for high reliability
- Peak OFF-state (reverse) voltage : -100 to -600V
- Average ON-state current : 5A
- TO-220 package
- Weight : 2g

Absolute Maximum Ratings at Ta = 25°C

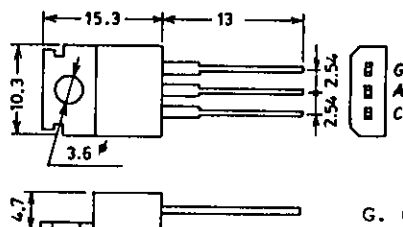
		DRA5B	DRA5C	DRA5E	DRA5G	unit
Repetitive Peak OFF-State Voltage	V_{DRM}	100	200	400	600	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}	-150	-300	-500	-700	V
Repetitive Peak Reverse Voltage	V_{RRM}	-100	-200	-400	-600	V
Average ON-State Current	$I_{T(AV)}$	Tc = 91°C, single-phase half-wave		→	→	5 A
RMS ON-State Current	$I_{T(RMS)}$	Sine half-wave		→	→	7.8 A
Surge ON-State Current	I_{TSM}	1 cycle, 50Hz		→	→	80 A
Amperes Squared-Seconds	$\int i^2 T \cdot dt$	→	→	→	→	32 A ² S
Peak Gate Power Dissipation	P_{GM}	→	→	→	→	5 W
Average Gate Power Dissipation	$P_{G(AV)}$	→	→	→	→	0.5 W
Peak Gate Forward Current	I_{FGM}	→	→	→	→	2 A
Peak Gate Forward Voltage	V_{FGM}	→	→	→	→	10 V
Peak Gate Reverse Voltage	V_{RGM}	→	→	→	→	5 V
Junction Temperature	T_j	→	→	→	→	125 °C
Storage Temperature	T_{stg}	→	→	→	→	-40 to +125 °C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Repetitive Peak OFF-State Current	I_{DRM}	Tj = 125°C, $V_D = V_{DRM}$			2	mA
Repetitive Peak Reverse Current	I_{RRM}	Tj = 125°C, $V_R = V_{RRM}$			2	mA
ON-State Voltage	V_T	$I_T = 15A$			1.6	V
Critical Rate of Rise of OFF-State Voltage	dv/dt	Tc = 125°C, $V_D = 2/3V_{DRM}$	30			V/μs
Holding Current	I_H	$R_L = 100\Omega$			60	mA
Gate Trigger Current	I_{GT}	$V_D = 6V, R_L = 10\Omega$			40	mA
Gate Trigger Voltage	V_{GT}	$V_D = 6V, R_L = 10\Omega$			1.5	V
Gate Nontrigger Voltage	V_{GD}	Tc = 125°C, $V_D = 2/3V_{DRM}$	0.2			V
Thermal Resistance	$R_{th(j-c)}$				3	°C/W

Package Dimensions 1104

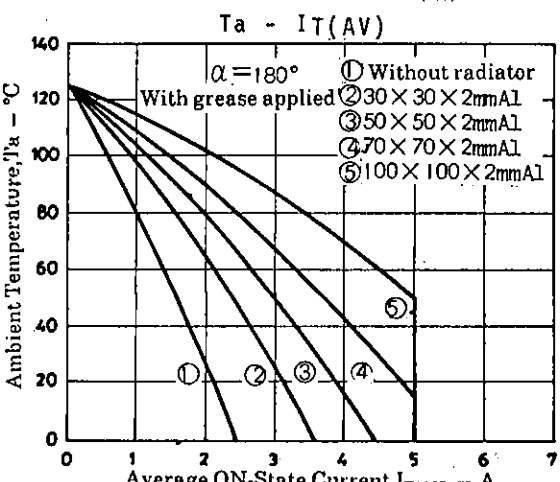
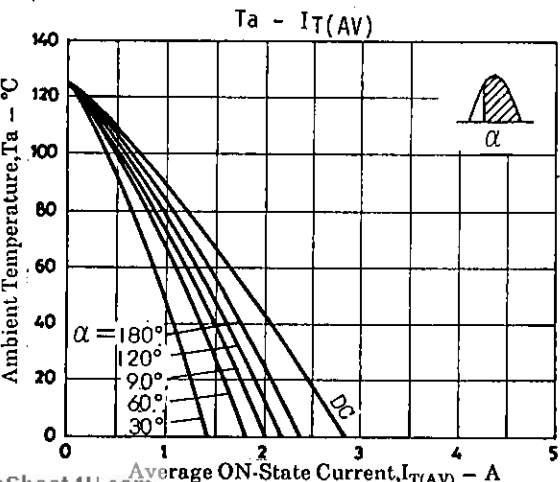
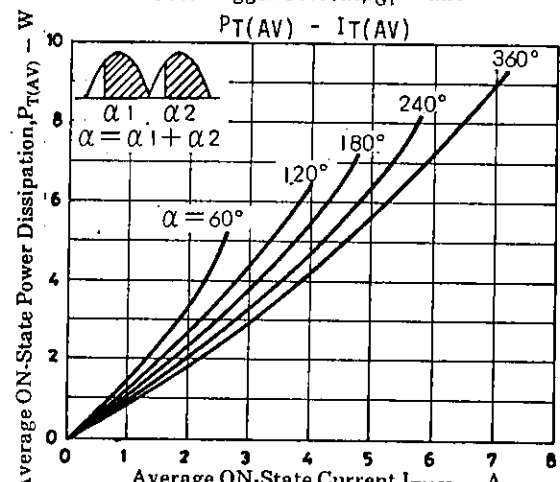
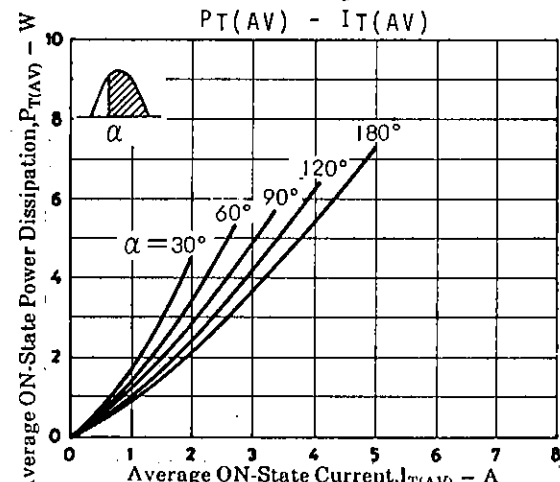
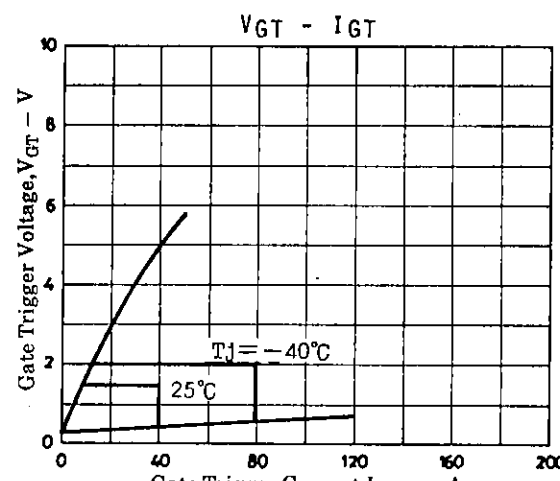
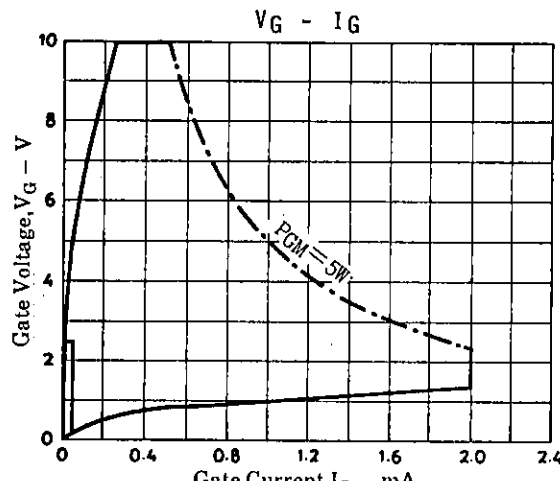
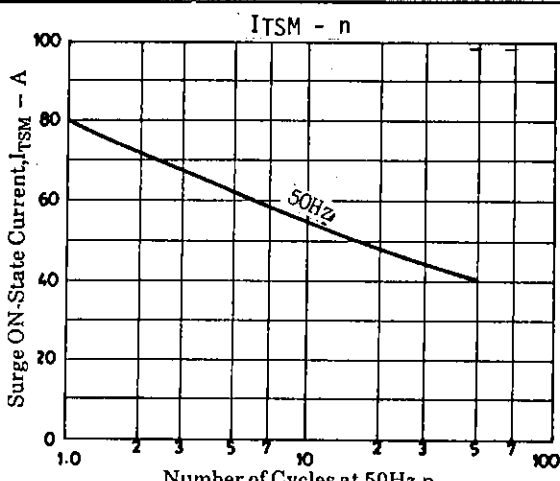
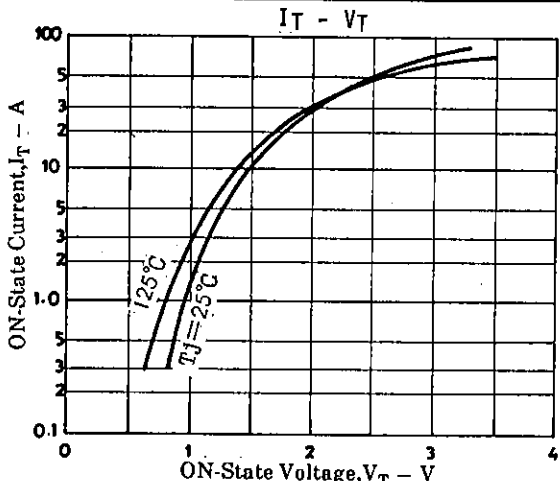
(unit: mm)

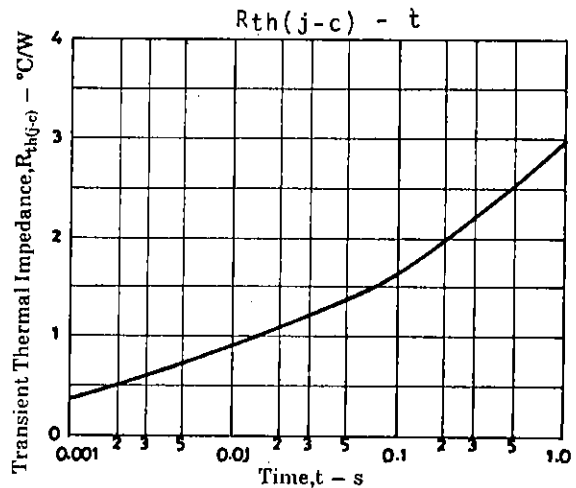
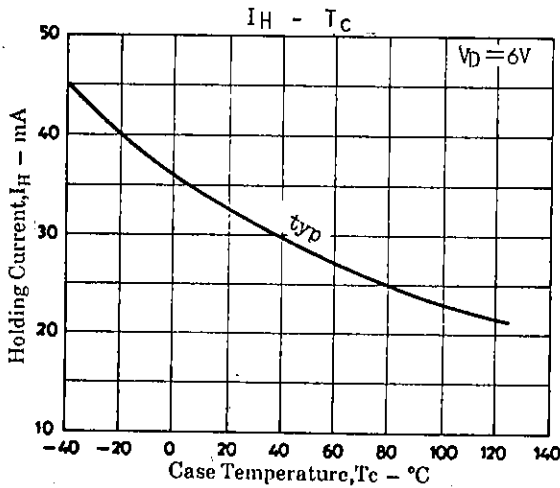
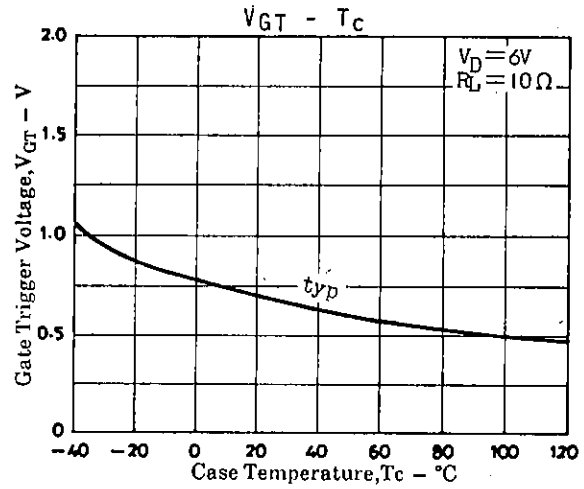
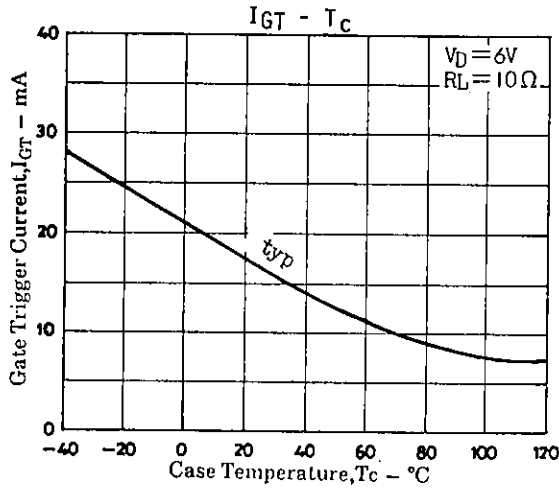
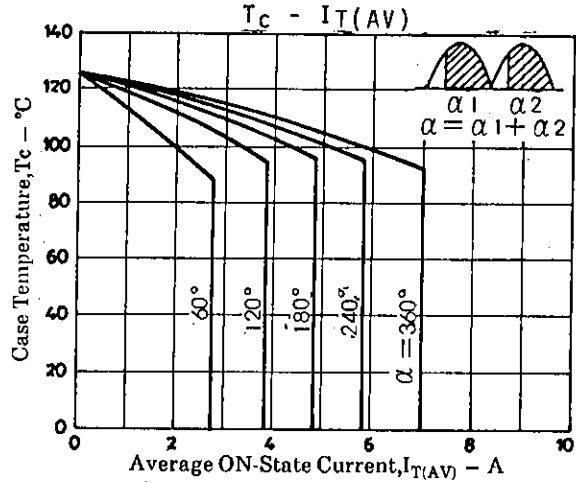
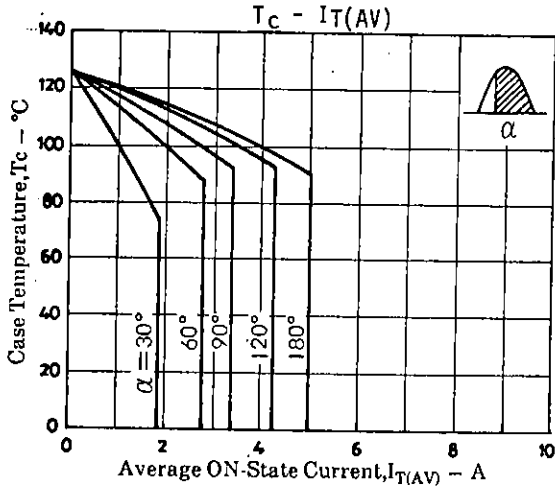


G. Gate
A. Anode
C. Cathode

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